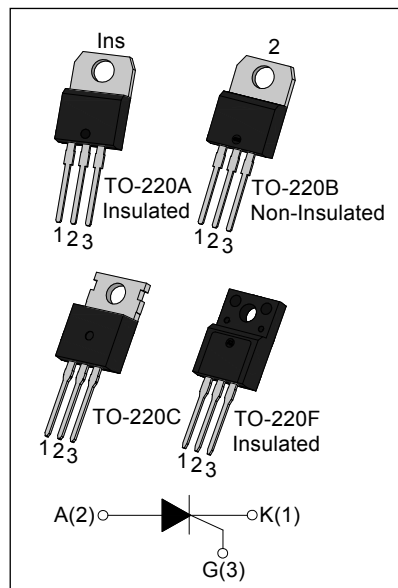




### DESCRIPTION:

With high ability to withstand the shock loading of large current, JCTx25 SCRs provide high dv/dt rate with strong resistance to electromagnetic interference. They are especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc.

From all three terminals to external heatsink, JCTx25A provides a rated insulation voltage of 2500 V<sub>RMS</sub>, and JCTx25F provides a rated insulation voltage of 2000 V<sub>RMS</sub>, complying with UL standards (File ref: E252906). All the packages mentioned are RoHS compliant. (2011/65/EU)



### MAIN FEATURES

Symbol	JCT625	JCT825
V <sub>DRM</sub> / V <sub>R<sub>RRM</sub></sub>	600V	800V
I <sub>T(RMS)</sub>	25A	
I <sub>GT</sub>	≤40mA	

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40-150	°C
Operating junction temperature range	T <sub>j</sub>	-40-150	°C
Repetitive peak off-state voltage(T <sub>j</sub> =25°C)	V <sub>DRM</sub>	600/800	V
Repetitive peak reverse voltage(T <sub>j</sub> =25°C)	V <sub>R<sub>RRM</sub></sub>	600/800	V
RMS on-state current	TO-220A(Ins)/ TO-220F(Ins) (T <sub>C</sub> =95°C)	25	A
	TO-220B(Non-Ins)/ TO-220C(T <sub>C</sub> =115°C)		
Non repetitive surge peak on-state current (tp=10ms)	I <sub>TSM</sub>	300	A
I <sup>2</sup> t value for fusing (tp=10ms)	I <sup>2</sup> t	450	A <sup>2</sup> s

Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )	dI/dt	50	A/ $\mu$ s
Peak gate current	$I_{GM}$	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	5	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	-	-	40	mA
$V_{GT}$		-	-	1.3	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=150^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	0.2	-	-	V
$I_L$	$I_G=1.2I_{GT}$	-	-	90	mA
$I_H$	$I_T=500\text{mA}$	-	-	80	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=150^\circ\text{C}$	200	-	-	V/ $\mu$ s

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=50\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	$\mu\text{A}$
$I_{RRM}$		$T_j=150^\circ\text{C}$	4	mA

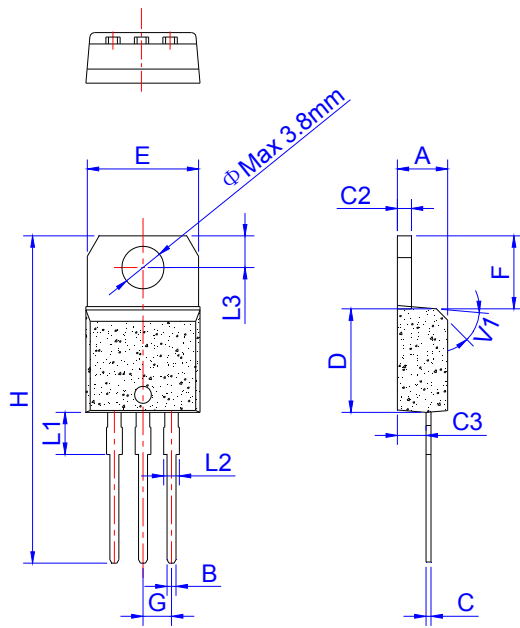
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)/ TO-220F(Ins)	1.7	$^\circ\text{C/W}$
		TO-220B(Non-Ins)/ TO-220C	1.0	

ORDERING INFORMATION

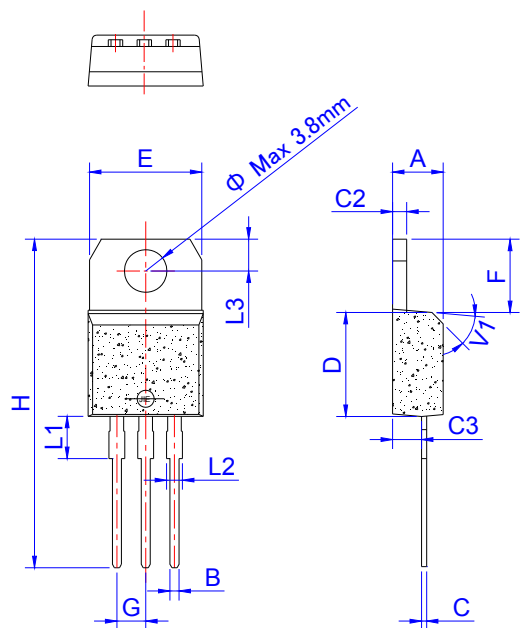
<p><b>J</b></p> <p>JieJie Microelectronics Co.,Ltd</p>	<p><b>CT</b></p> <p>SCRs</p> <p>6:VDRM /VRRM ≥600V 8:VDRM /VRRM ≥800V</p>	<p><b>6</b></p>	<p><b>25</b></p> <p>I<sub>T(RMS)</sub>:25A</p>	<p><b>B</b></p> <p>A:TO-220A(Ins) F:TO-220F(Ins) B:TO-220B(Non-Ins) C:TO-220C</p>
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PACKAGE MECHANICAL DATA



TO-220A Ins

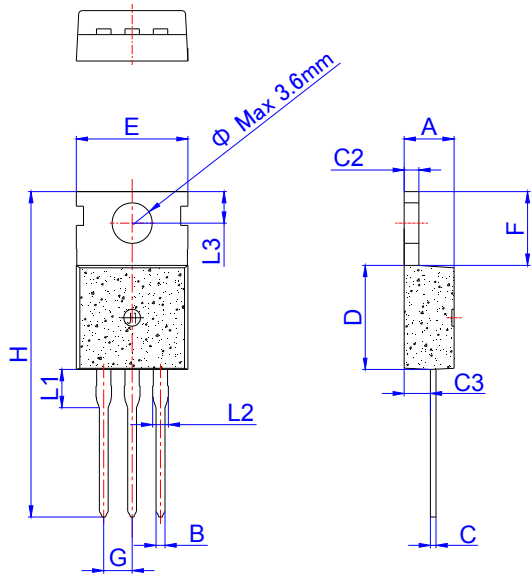
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220B Non-Ins

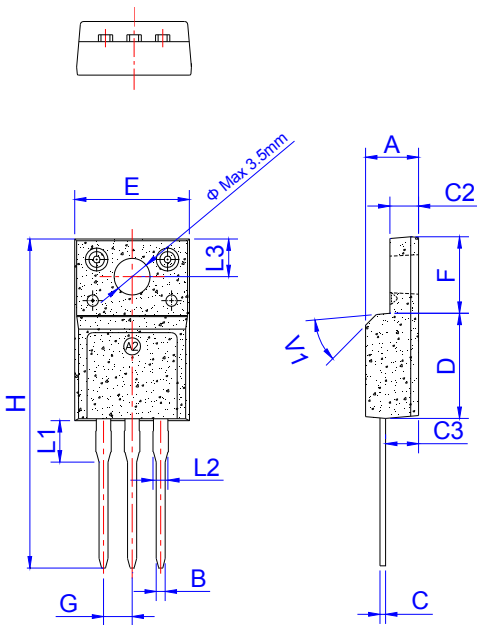
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-220C

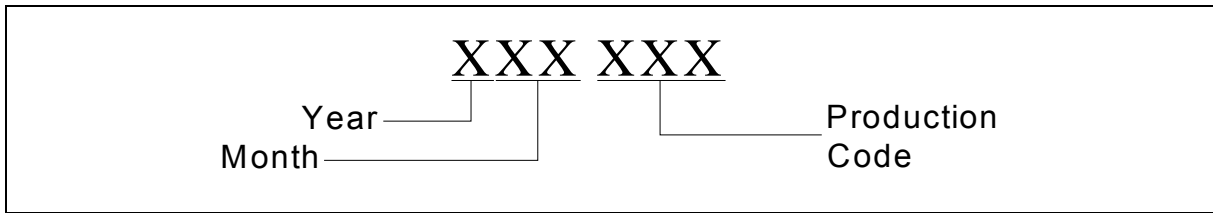
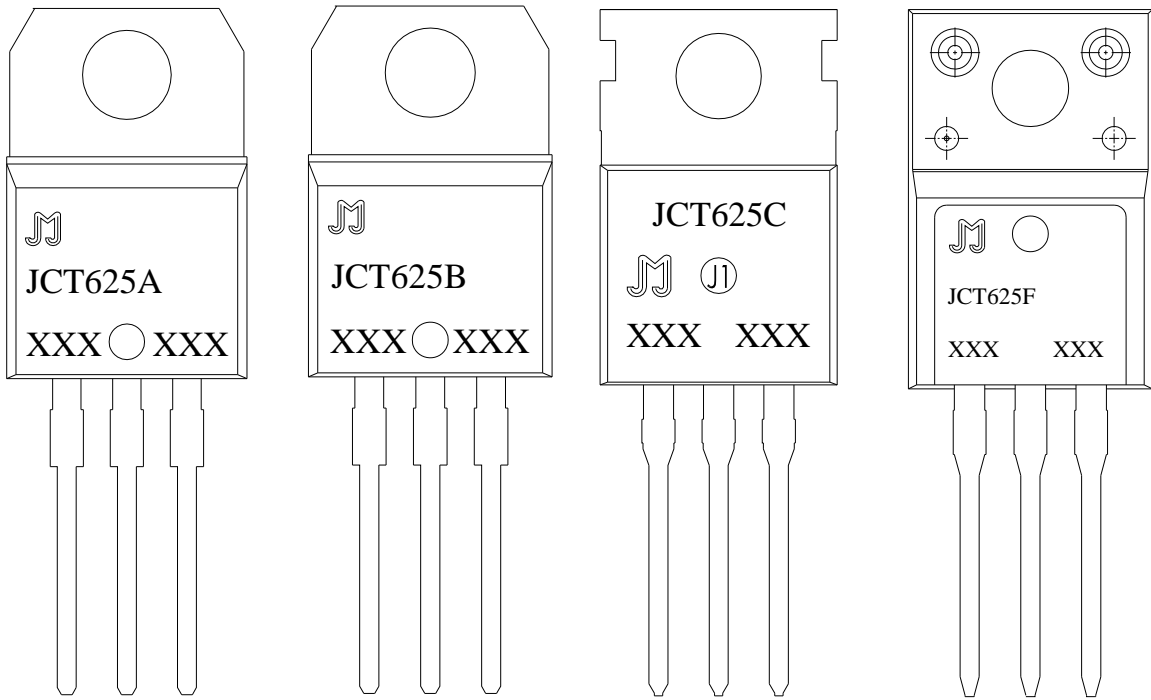
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

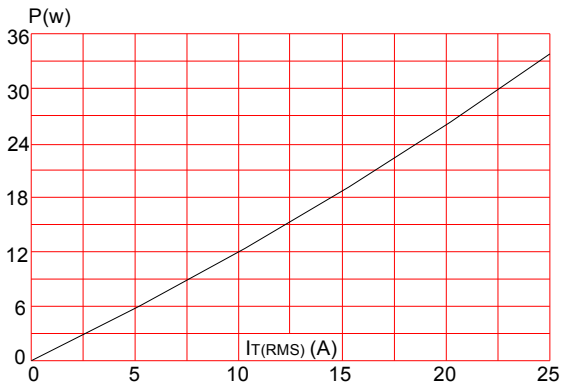
**MARKING**



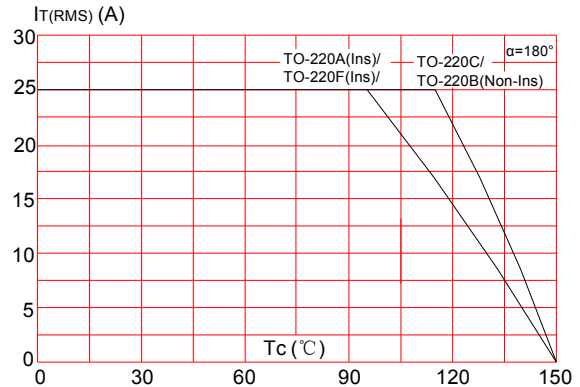
**PACKAGE INFORMATION**

PACKAGE	WEIGHT (PER PCS)	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	2.308g	TUBE	50	1,000	8,000
TO-220B	1.935g	TUBE	50	1,000	8,000
TO-220C	2.05g	TUBE	50	1,000	8,000
TO-220F	2.093g	TUBE	50	1,000	8,000

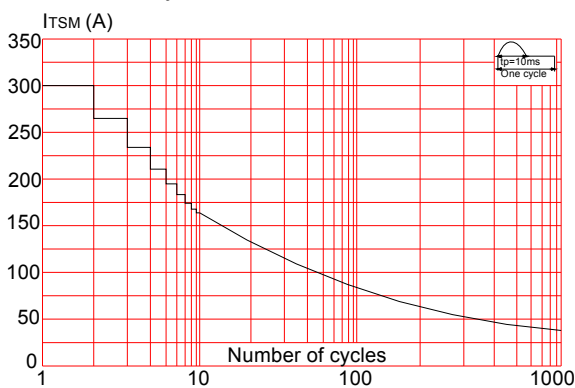
**FIG.1:** Maximum power dissipation versus RMS on-state current



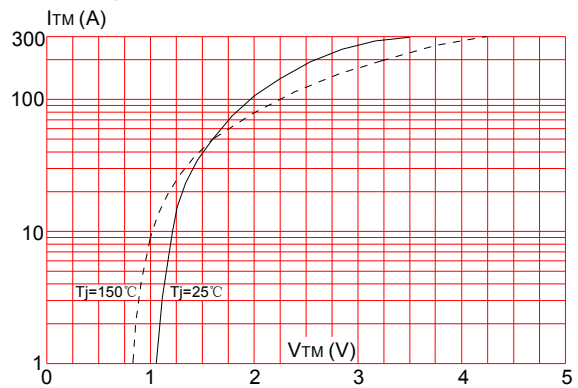
**FIG.2:** RMS on-state current versus case temperature



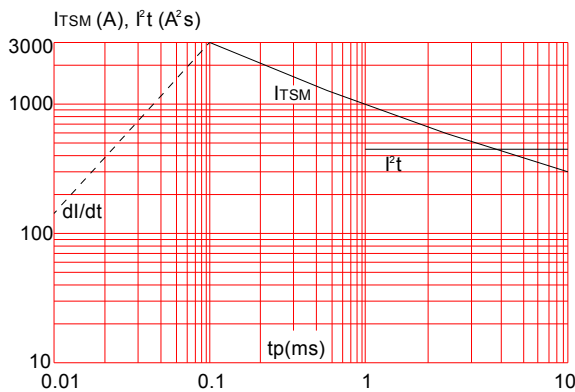
**FIG.3:** Surge peak on-state current versus number of cycles



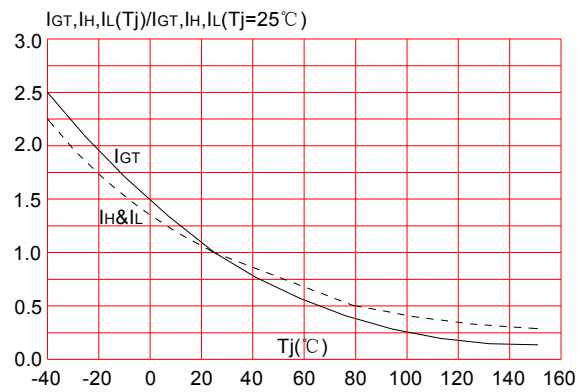
**FIG.4:** On-state characteristics (maximum values)




**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



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